

ABSTRACT OF THE DISCLOSURE

A wafer polishing method is provided. A first polishing pad comprising a plurality of abrasive units is provided. A first polishing operation is performed on the first polishing pad to planarize a wafer. Thereafter, a second polishing pad comprising
5 a plurality of abrasive units is provided. The surface of the abrasive unit in contact with the wafer is roughened. A second polishing operation is performed on the second polishing pad. Since a second polishing operation using a second polishing pad with a roughened surface is performed, gradual reduction of polishing rate as the polish layer is planarized can be avoided.

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